

REMARKS

Entry and consideration of this amendment are requested. The amendments to claims 9-12 and 14 address the pending rejections under 35 USC §112, ¶¶ 1 and 2. In the Advisory Action mailed April 1, 2003, the Examiner maintained these rejections on the basis that the claim language "free of metal contaminants" was not supported by the specification and was indefinite. Applicant reiterates the arguments made in the previously-filed amendment with respect to the prior art rejections of record.

With this amendment, applicant submits that the claims are now in compliance with §112. Specifically, the specification explains, page 1, lines 12-23, that the prior art process of using a Kaufman ion source causes metal contamination of the substrate due to metal sputtering off of the metal grid used in that process. The specification further explains, page 10, lines 6-13, the plasma source ion implantation (PSII) technique does not use a metal grid and thus reduces the possibility of metal contamination of the substrate. Thus, applicant submits that there is clear support in the specification as filed for the claim recitation that the silicon dioxide and semiconductor substrate layers, respectively, are free of sputtered metal contaminants. This clearly follows from the discussion of the prior art process that did produce sputtered metal contaminants and the PSII process that does not.

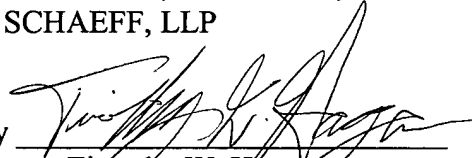
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With the entry of the previously-filed amendment after final rejection and the present amendment, applicant submits that claims 9-12 and 14 are in condition for allowance. Early notification to that effect is respectfully solicited.

Respectfully submitted,

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